

1 GBPS TO 4.25 GBPS MULTI-RATE VCSEL DRIVER

FEATURES

- Multi-Rate Operation from 1 Gbps Up To 4.25 Gbps
- 2-Wire Digital Interface
- Digitally Selectable Modulation Current
- Digitally Selectable Bias Current
- Automatic Power Control (APC) Loop
- Supports Transceiver Management System (TMS)
- Includes Laser Safety Features
- Analog Temperature Sensor Output
- Single 3.3-V Supply

- Operating Temperature -40°C to 85°C

- Small Footprint Surface Mount 4 mm \times 4 mm, 20-Pin QFN Package

APPLICATIONS

- Multirate SFP/SFF Modules
- 1.0625 Gbps, 2.125 Gbps, and 4.25 Gbps Fibre Channel Transmitters
- Gigabit Ethernet Transmitters

DESCRIPTION

The ONET4291VA is a versatile high-speed multi-rate VCSEL driver for fiber optic applications with data rates up to 4.25 Gbps.

The device provides a 2-wire interface which allows digital control of the modulation and bias currents, eliminating the need for of external components.

The ONET4291VA includes an integrated automatic power control loop as well as circuitry to support laser safety and transceiver management systems.

The part is available in a small footprint 4 mm \times 4 mm 20-pin QFN package and it requires a single 3.3-V supply.

This power efficient multi-rate VCSEL driver is characterized for operation from -40°C to 85°C ambient temperature.

BLOCK DIAGRAM

A simplified block diagram of the ONET4291VA is shown in [Figure 1](#).

This compact, low power 1-Gbps to 4.25-Gbps multi-rate VCSEL driver consists of a high-speed current modulator, a modulation current generator, power-on reset circuitry, a 2-wire interface and control logic block, a bias current generator and automatic power control loop, and an analog reference block.



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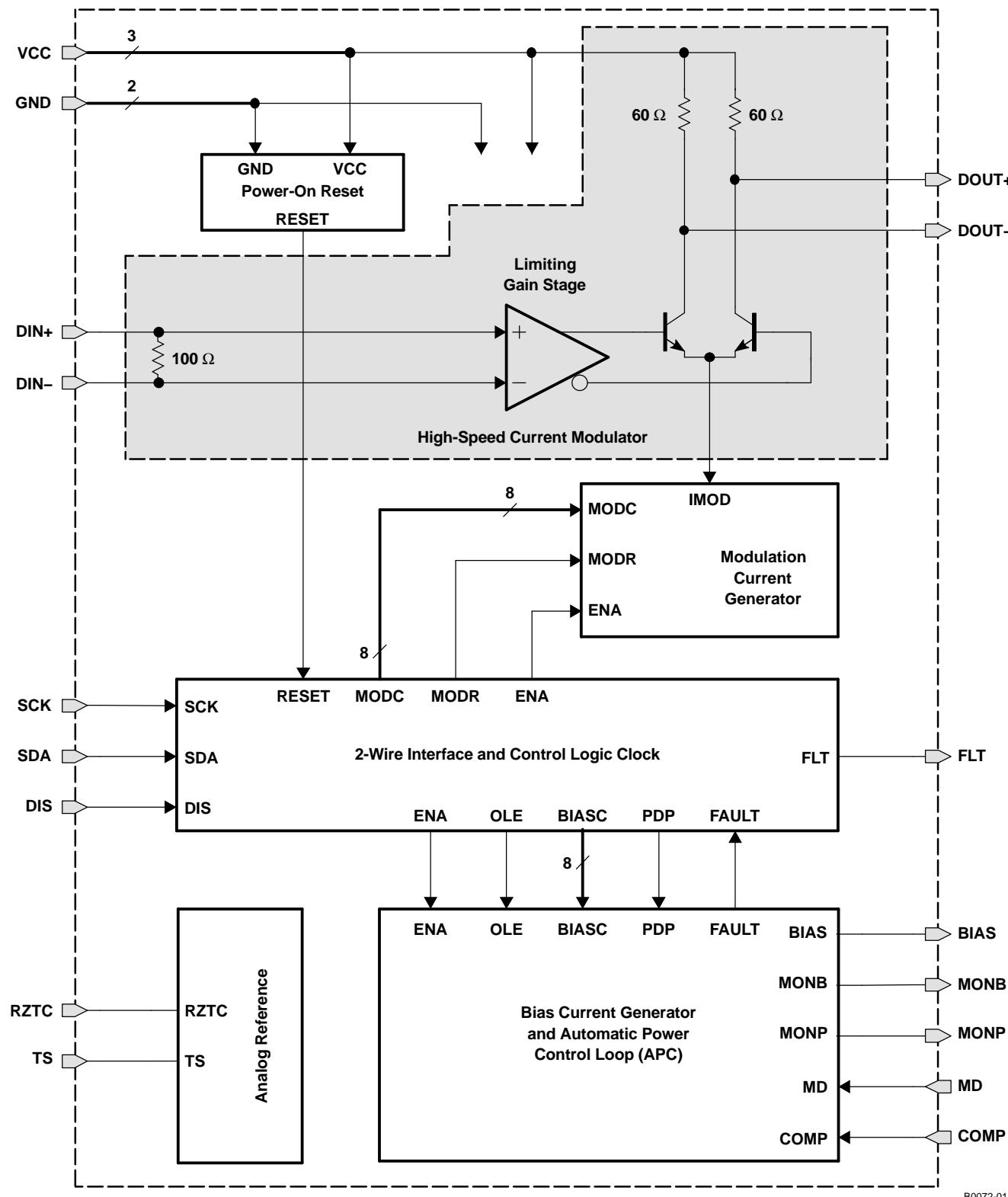


Figure 1. Simplified Block Diagram of the ONET4291VA

HIGH-SPEED CURRENT MODULATOR

The data signal is applied to the high-speed current modulator by means of the input signal pins DIN+/DIN-, which provide on-chip differential 100- Ω line-termination. The succeeding limiting gain stage ensures sufficient drive amplitude and edge-speed for driving the current modulator differential pair.

The modulation current is sunk from the common emitter node of the differential pair by means of a modulation current generator, which is digitally controlled by the 2-wire interface and control logic block.

The collector nodes of the differential pair are connected to the output pins DOUT+/DOUT-, which include on-chip 2 \times 60- Ω back-termination to VCC. The 60- Ω back-termination helps to sufficiently suppress signal distortion caused by double reflections for VCSEL diodes with impedances ranging from 50 Ω through 75 Ω .

MODULATION CURRENT GENERATOR

The modulation current generator provides the current for the current modulator described above. The circuit is digitally controlled by the 2-wire interface and control logic block.

An 8-bit wide control bus, MODC, is used to set the desired modulation current.

Furthermore, two modulation current ranges are selected by means of the MODR signal.

The ENA signal enables or disables the modulation current generator.

The modulation current can be disabled by setting the DIS input pin to a high level. The modulation current is also disabled in a fault condition if the fault detection enable register flag FLTEN is set.

For more information about the register functionality, see the register mapping description.

2-WIRE SERIAL INTERFACE AND CONTROL LOGIC

The ONET4291VA uses a 2-wire serial interface for digital control. A simplified block diagram of this interface is shown in [Figure 2](#).

The two circuit inputs, SDA and SCK, are driven, respectively, by the serial data and serial clock from a microprocessor, for example. Both inputs include 100-k Ω pullup resistors to VCC. For driving these inputs, an open drain output is recommended.

A write cycle consists of a START command, three address bits with MSB first, eight data bits with MSB first, and a STOP command. In idle mode, both SDA and SCK lines are at a high level.

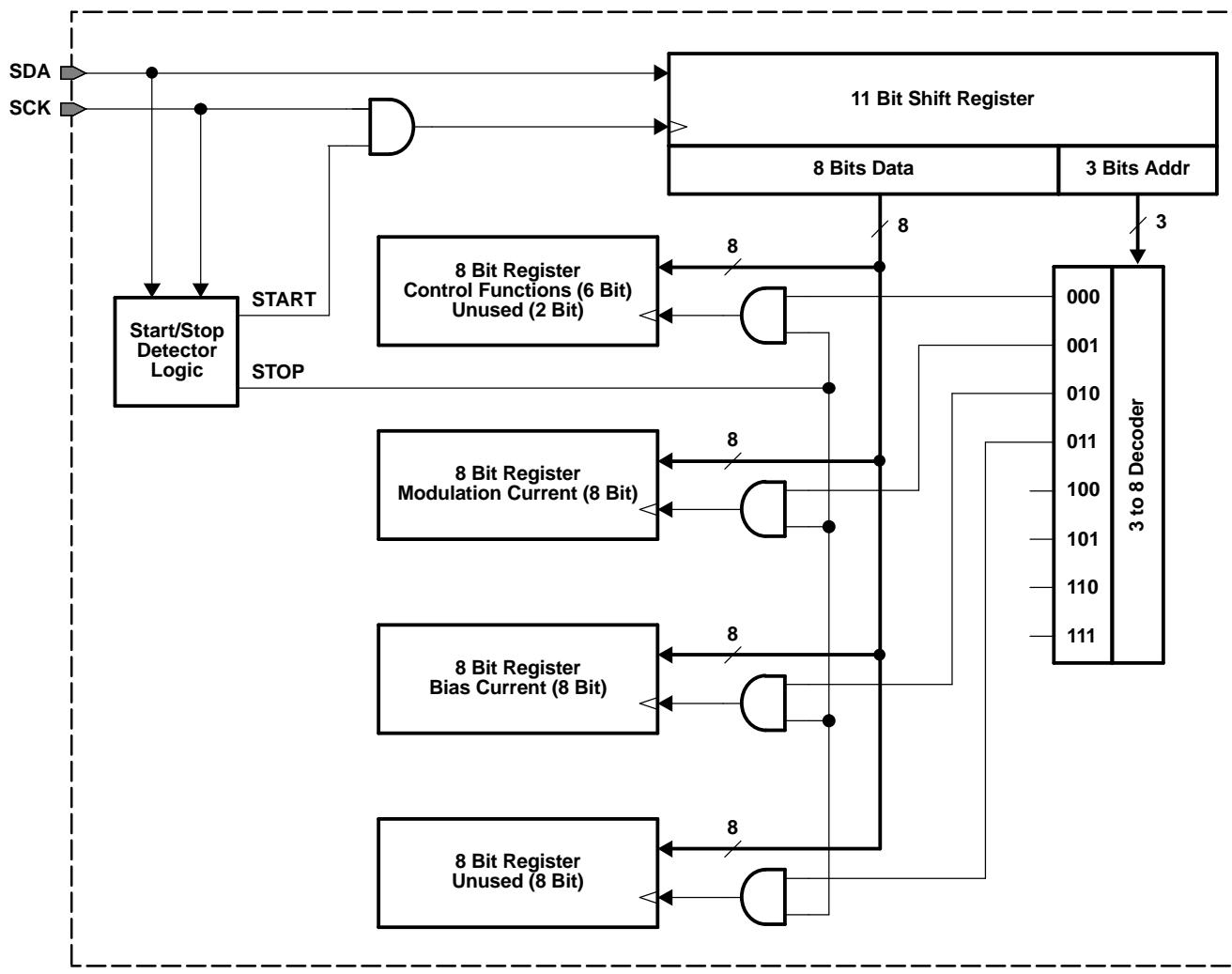
A START command is initiated by the falling edge of SDA with SCK at a high level, transitioning to a low level.

Bits are clocked into an 11-bit wide shift register during the high level of the system clock SCK.

A STOP command is detected on the rising edge of SDA after SCK has changed from a low to a high level.

At the time of detection of a STOP command, the eight data bits from the shift register are copied to a selected 8-bit register. Register selection occurs according to the three address bits in the shift register, which are decoded to eight independent select signals using a 3 to 8 decoder block.

In the ONET4291VA, only addresses 0 (000b) through 3 (011b) are used.



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Figure 2. Simplified 2-Wire Interface Block Diagram

The timing definition for the serial data signal SDA and the serial clock signal SCK is shown in [Figure 3](#).

The corresponding timing requirements are listed in [Table 1](#).

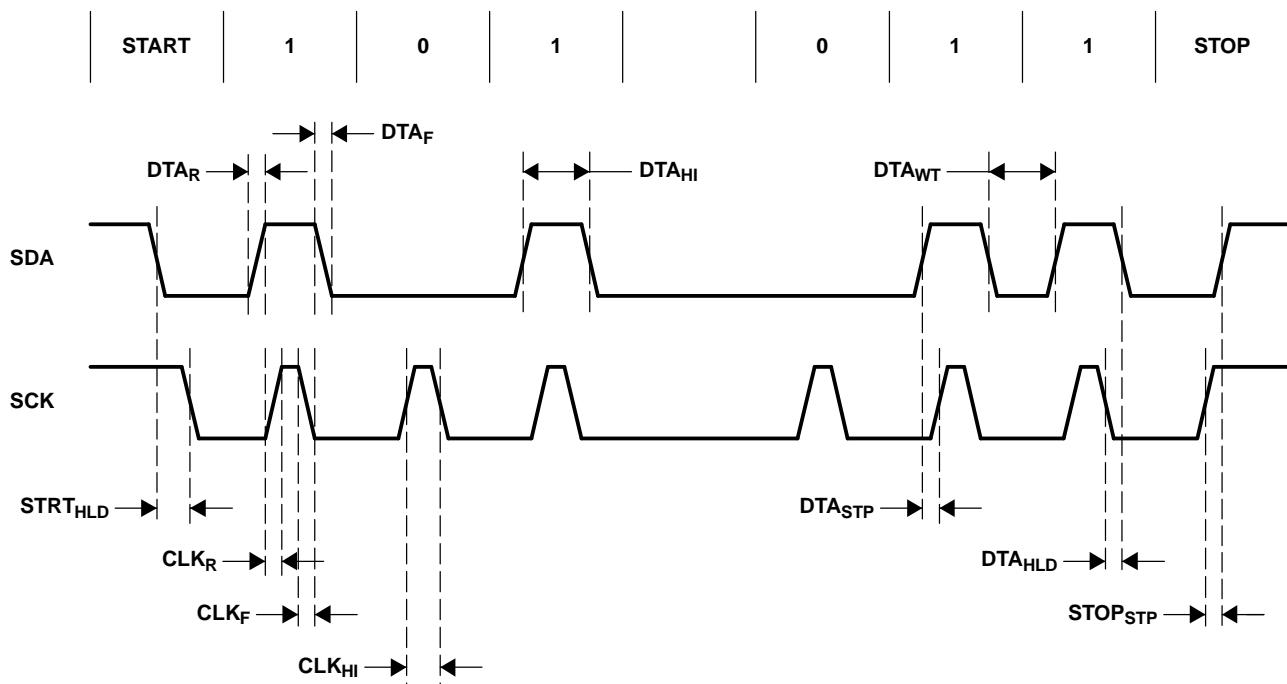


Figure 3. 2-Wire Interface Timing Diagram

Table 1. 2-Wire Interface Timing

PARAMETER	DESCRIPTION	MIN	MAX	UNIT
$STRT_{HLD}$	START hold time	Time required from data falling edge to clock falling edge at START	10	ns
CLK_R , DTA_R	Clock and data rise time	Clock and data rise time		10 ns
CLK_F , DTA_F	Clock and data fall time	Clock and data fall time		10 ns
CLK_{HI}	Clock high time	Minimum clock high period	50	ns
DTA_{HI}	Data high time	Minimum data high period	100	ns
DTA_{STP}	Data setup time	Minimum time from data rising edge to clock rising edge	10	ns
DTA_{WT}	Data wait time	Minimum time from data falling edge to data rising edge	50	ns
DTA_{HLD}	Data hold time	Minimum time from clock falling edge to data falling edge	10	ns
$STOP_{STP}$	STOP setup time	Minimum time from clock rising edge to data rising edge at STOP	10	ns

REGISTER MAPPING

The register mapping for the register addresses 0 (000b) through 3 (011b) are shown in [Table 2](#) to [Table 5](#). Register 3 is included for future enhancements. It is not used in the current device.

Table 6 describes the circuit functionality based on the register settings.

Table 2. Register 0 (000b) Mapping

address 0 (0000b)							
bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
ENA	PDP	PDR	OLE	FLTEN	MODR	–	–

Table 3. Register 1 (001b) Mapping

address 1 (001b)							
bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
MODC7	MODC6	MODC5	MODC4	MODC3	MODC2	MODC1	MODC0

Table 4. Register 2 (010b) Mapping

address 2 (010b)							
bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
BIASC7	BIASC6	BIASC5	BIASC4	BIASC3	BIASC2	BIASC1	BIASC0

Table 5. Register 3 (011b) Mapping

address 3 (011b)							
bit 7	bit 6	bit 5	bit 4	bit 3	bit 2	bit 1	bit 0
—	—	—	—	—	—	—	—

Table 6. Register Functionality

Symbol	Register	Function
ENA	Enable	Enables chip when set to 1. Can be toggled to reset a fault condition.
PDP	Photodiode polarity	Photodiode polarity bit: 1 = common anode 0 = common cathode
PDR	Photodiode current range	Photodiode current range bit: 1 = 0 μ A – 500 μ A with 2- μ A resolution 0 = 0 μ A – 250 μ A with 1- μ A resolution
OLE	Open loop enable	Open loop enable bit: 1 = open loop bias current control 0 = closed loop bias current control
FLTEN	Fault detection enable	Fault detection enable bit: 1 = fault detection on 0 = fault detection off
MODR	Modulation current range	Laser modulation current range: 1 = 0 mA – 15 mA 0 = 0 mA – 12 mA
MODC7	Modulation current bit 7 (MSB)	Modulation current setting:
MODC6	Modulation current bit 6	
MODC5	Modulation current bit 5	MODR = 1 (see above):
MODC4	Modulation current bit 4	Modulation current: 100 μ A – 15.4 mA with 68 μ A step size
MODC3	Modulation current bit 3	
MODC2	Modulation current bit 2	MODR = 0 (see above):
MODC1	Modulation current bit 1	Modulation current: 100 μ A – 12 mA with 51 μ A step size
MODC0	Modulation current bit 0 (LSB)	
BIASC7	Bias current bit 7 (MSB)	closed loop (APC):
BIASC6	Bias current bit 6	Coupling ratio CR between VCSEL bias current and photodiode current is: $CR = I_{BIAS-VCSEL} / I_{PD}$
BIASC5	Bias current bit 5	$PDR = 0$ (see above), $BIASC = 0 \dots 255$, $I_{BIAS-VCSEL} \leq 12$ mA:
BIASC4	Bias current bit 4	$I_{BIAS-VCSEL} = 100 \mu A + (1 \mu A \times CR \times BIASC)$
BIASC3	Bias current bit 3	$PDR = 1$ (see above), $BIASC = 0 \dots 255$, $I_{BIAS-VCSEL} \leq 12$ mA:
BIASC2	Bias current bit 2	$I_{BIAS-VCSEL} = 100 \mu A + (2 \mu A \times CR \times BIASC)$
BIASC1	Bias current bit 1	
BIASC0	Bias current bit 0 (LSB)	open loop: $I_{BIAS-VCSEL} = 100 \mu A + (47 \mu A \times BIASC)$

BIAS CURRENT GENERATION AND APC LOOP

The bias current generation and APC loop are controlled by means of the 2-wire interface.

In open loop operation, selected by setting OLE = 1 (bit 4 of register 0), the bias current is set directly by the 8-bit wide control word BIASC[0..7] (register 2).

In automatic power control mode, selected by setting OLE = 0, the bias current depends on the register settings BIASC[0..7] and the coupling ratio (CR) between the VCSEL bias current and the photodiode current. $CR = I_{BIAS-VCSEL} / I_{PD}$.

Two photodiode current ranges can be selected by means of the PDR register (bit 5 of register 0). The photodiode range should be chosen to keep the laser bias control DAC close to the center of its range. This keeps the laser bias current setpoint resolution high and the loop settling time constant within specification.

For details regarding the bias current setting in open loop as well as in closed loop mode, see [Table 6](#).

In closed loop mode, the photodiode polarity bit, PDP, must be set for common anode or common cathode configuration to ensure proper operation. In open loop mode if a photodiode is still present, the photodiode polarity bit must be set to the opposite setting.

ANALOG REFERENCE

The ONET4291VA is supplied by a single 3.3-V $\pm 10\%$ supply voltage connected to the VCC pins. This voltage is referenced to ground (GND).

On-chip bandgap voltage circuitry generates a reference voltage, independent of the supply voltage, from which all other internally required voltages and bias currents are derived.

An external zero temperature coefficient resistor must be connected from the RZTC pin of the device to ground (GND). This resistor is used to generate a precise zero TC current which is used as a reference current for the on-chip DACs.

In order to minimize the module component count, the ONET4291VA VCSEL driver provides an on-chip temperature sensor. The output voltage of the temperature sensor is available at the TS pin.

The voltage is $V_{TS} = 9.4 \text{ mV} \times \text{TEMP} + 1337 \text{ mV}$ with TEMP given in $^{\circ}\text{C}$.

Note that the voltage at TS is not buffered. As a result, TS can only drive capacitive loads.

POWER-ON RESET AND REGISTER LOADING SEQUENCE

The ONET4291VA has power on reset circuitry which ensures that all registers are reset to zero during startup. After the power-on to initialize time (T_{INIT1}), the internal registers are ready to be loaded. It is important that the registers are loaded in the following order:

1. Bias current register (register 2, 010b),
2. Modulation current register (register 1, 001b),
3. Control register (register 0, 000b).

The part will be ready to transmit data after the initialize to transmit time T_{INIT2} , assuming that the control register enable bit ENA is 1 and the disable pin DIS is low.

The ONET4291VA can be disabled using either the ENA control register bit or the disable pin DIS. In both cases the internal registers are not reset. After the disable pin DIS is de-asserted and/or the enable bit ENA is re-asserted the part returns to its prior output settings.

LASER SAFETY FEATURES AND FAULT RECOVERY PROCEDURE

The ONET4291VA provides built in laser safety features. The following fault conditions are detected:

1. Voltage at MONB exceeds 1.2 V,
2. Photodiode current exceeds 150% of its target value,
3. Bias control DAC drops in value by more than 33% in one step.

If one or more fault conditions occur and the fault enable bit FLTN is set to 1, the ONET4192VA responds by:

1. Setting the VCSEL bias current to zero.

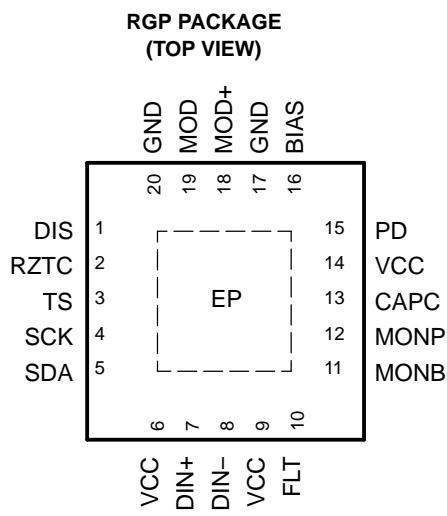
2. Setting the modulation current to zero.
3. Asserting and latching the FLT pin.

Fault recovery is performed by the following procedure:

1. The disable pin DIS and/or the enable control bit ENA are toggled for at least the fault latch reset time T_{RESET} .
2. The FLT pin de-asserts while the disable pin DIS is asserted or the enable bit ENA is de-asserted.
3. If the fault condition is no longer present, the part will return to normal operation with its prior output settings after the disable negate time T_{ON} .
4. If the fault condition is still present, FLT re-asserts once DIS is set to low level and the part will not return to normal operation.

PACKAGE

For the ONET4291VA, a small footprint 4 mm × 4 mm 20-pin QFN package with a lead pitch of 0,5 mm is used. The pin out is shown in [Figure 4](#).



P0031-01

Figure 4. Pinout of ONET4291VA in a 4 mm × 4 mm 20-Pin QFN Package

TERMINAL FUNCTIONS

TERMINAL NO.	NAME	TYPE	DESCRIPTION
1	DIS	CMOS-in	Disables both bias and modulation current when set to high state. Toggle to reset a fault condition
2	RZTC	Analog	Connect external zero TC 30-kΩ to ground (GND). Used to generate a defined zero TC reference current for internal DACs.
3	TS	Analog-out	Temperature sensor output. Not buffered, capacitive load only.
4	SCK	CMOS-in	2-wire interface serial clock. Includes a 100-kΩ pullup resistor to VCC.
5	SDA	CMOS-in	2-wire interface serial data input. Includes a 100-kΩ pullup resistor to VCC.
6, 9, 14	VCC	Supply	3.3-V ±10% supply voltage
7	DIN+	Analog-in	Non-inverted data input. On-chip differentially 100-Ω terminated to DIN-. Must be ac coupled.
8	DIN-	Analog-in	Inverted data input. On-chip differentially 100-Ω terminated to DIN+. Must be ac coupled.
10	FLT	CMOS-out	Fault detection flag
11	MONB	Analog-out	Bias current monitor. Sources an 8.3% replica of the bias current. Connect an external resistor to ground (GND). If the voltage at this pin exceeds 1.2 V a fault is triggered.

TERMINAL FUNCTIONS (continued)

TERMINAL		TYPE	DESCRIPTION
NO.	NAME		
12	MONP	Analog-out	Photodiode current monitor. Sources a 50% replica of the photodiode current. Connect an external resistor to ground (GND).
13	CAPC	Analog	Compensation pin used to control the bandwidth of the APC loop. Connect a 0.01- μ F capacitor to ground.
15	PD	Analog	Monitor photodiode input. The pin can source or sink current dependent on PDP register setting. Pin supplies >1.5-V reverse bias.
16	BIAS	Analog	VCSEL diode bias current source. Connect to laser anode through inductor. Murata BLM15HG102SN1 is recommended.
17, 20, EP	GND	Supply	Circuit ground. The exposed die pad (EP) must be grounded.
18	MOD+	CML-out	Non-inverted modulation current output. AC coupled to anode of common cathode VCSEL. On-chip 60- Ω back-terminated to VCC.
19	MOD-	CML-out	Inverted modulation current output. AC coupled through VCSEL matching resistor to ground (GND). On-chip 60- Ω back-terminated to VCC.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		VALUE / UNIT
V_{CC}	Supply voltage	-0.3 V to 4 V
V_{DIS} , V_{RZTC} , V_{TS} , V_{SCK} , V_{SDA} , V_{DIN+} , V_{DIN-} , V_{FLT} , V_{MONB} , V_{MONP} , V_{CAPC} , V_{PD} , V_{BIAS} , V_{MOD+} , V_{MOD-}	Voltage at DIS, RZTC, TS, SCK, SDA, DIN+, DIN-, FLT, MONB, MONP, CAPC, PD, BIAS, MOD+, MOD- ⁽²⁾	-0.3 V to 4 V
ESD	ESD rating at all pins	3 kV (HBM)
$T_{J,max}$	Maximum junction temperature	125°C
T_{STG}	Storage temperature range	-65°C to 85°C
T_A	Characterized free-air operating temperature range	-40°C to 85°C
T_{LEAD}	Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	260°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to network ground terminal.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V_{CC}	Supply voltage	2.9	3.3	3.6	V
V_{IH}	CMOS input high voltage	DIS, SCK, SDA	2		V
V_{IL}	CMOS input low voltage	DIS, SCK, SDA		0.8	V
	Bias output headroom voltage	$V_{CC} - V_{BIAS}$, $I_{BIAS} = 10$ mA	500		mV
	Photodiode current range	Control bit PDR = 1, step size = 2 μ A	10	500	μ A
		Control bit PDR = 0, step size = 1 μ A	5	250	
R_{RZTC}	Zero TC resistor value ⁽¹⁾	1.22-V bias across resistor	29.7	30	30.3
V_{IN}	Differential input voltage swing		200	800	2400
t_{R-IN}	Input rise time	20%-80%, $f_{BIT} = 1.25$ Gbps		160	ps
		20%-80%, $f_{BIT} \geq 2.125$ Gbps		100	
t_{F-IN}	Input fall time	20%-80%, $f_{BIT} = 1.25$ Gbps		160	ps
		20%-80%, $f_{BIT} \geq 2.125$ Gbps		100	
T_A	Operating free-air temperature		-40	85	°C

(1) Changing the value alters DAC ranges.

DC ELECTRICAL CHARACTERISTICS

over recommended operating conditions, all values are for open loop operation, $I_{MOD} = 6 \text{ mA}$, $I_{BIAS} = 5 \text{ mA}$, and $R_{RZTC} = 30 \text{ k}\Omega$, unless otherwise noted

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{CC}	Supply voltage	2.9	3.3	3.6	V
I_{VCC}	$I_{MOD} = 6 \text{ mA}$, $I_{BIAS} = 5 \text{ mA}$, including I_{MOD} and I_{BIAS}	40	45		mA
	Disabled, DIS = high and/or control bit ENA = low	22			
R_{IN}	Differential between DIN+/DIN-	85	100	115	Ω
R_{OUT}	Data output/output resistance	50	60	70	Ω
	CMOS input current	-50	10		μA
	CMOS input current	-10	10		μA
V_{OH}	CMOS output high voltage	2.5			V
V_{OL}	CMOS output low voltage	0.5			V
$I_{BIAS-DIS}$	Bias current during disable	100			μA
$I_{BIAS-MIN}$	Minimum bias current	0.2			mA
$I_{BIAS-MAX}$	DAC set to maximum, closed loop	8.5			mA
	DAC set to maximum, open loop	11			
V_{PD}	Photodiode reverse bias voltage	1.5	2.1		V
	Photodiode fault current level	150%			
V_{TS}	Temperature sensor voltage range	0.8	2.5		V
	Temperature sensor accuracy	± 3			$^{\circ}\text{C}$
I_{TS}	Temperature sensor drive current	-10	10		μA
	Photodiode current monitor ratio	45%	60%	80%	
	Bias current monitor ratio	6.7%	8.3%	10%	
V_{CC-RST}	V_{CC} reset threshold voltage	2.4	2.6	2.85	V
$V_{CC-RSTHYS}$	V_{CC} reset threshold voltage hysteresis	120			mV
$V_{MONB-FLT}$	Fault voltage at MONB	1.05	1.2	1.45	V

(1) The bias current can be set below the specified minimum according to the corresponding register setting described in the register mapping section above, however in closed loop operation settings below the specified value may trigger a fault.

(2) Assured by simulation over process, supply, and temperature variation.

AC ELECTRICAL CHARACTERISTICS

over recommended operating conditions with 50- Ω output load, open loop operation, $I_{MOD} = 6 \text{ mA}$, $I_{BIAS} = 5 \text{ mA}$, and $R_{RZTC} = 30 \text{ k}\Omega$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t_{R-OUT}	20%–80%, $t_{R-IN} = 160 \text{ ps}$, single-ended $V_{IN} > 400 \text{ mV}_{pp}$	60	125		ps
	20%–80%, $t_{R-IN} = 100 \text{ ps}$, single-ended $V_{IN} > 400 \text{ mV}_{pp}$	35	100		
t_{F-OUT}	20%–80%, $t_{F-IN} = 160 \text{ ps}$, single-ended $V_{IN} > 400 \text{ mV}_{pp}$	60	125		ps
	20%–80%, $t_{F-IN} = 100 \text{ ps}$, single-ended $V_{IN} > 400 \text{ mV}_{pp}$	35	100		
$I_{MOD-MAX}$	Control bit MODR = 1, 50- Ω load	11.5			mA
	Control bit MODR = 0, 50- Ω load	9			
$I_{MOD-STEP}$	Control bit MODR = 1, 50- Ω load	68			μA
	Control bit MODR = 0, 50- Ω load	51			
DJ	$f_{BIT} = 4.25 \text{ Gbps}$, excluding DJ caused by duty cycle distortion	7	20		ps_{p-p}
DCD	$f_{BIT} = 4.25 \text{ Gbps}$	8			ps_{p-p}

(1) Typical operating condition is at $V_{CC} = 3.3 \text{ V}$ and $T_A = 25^{\circ}\text{C}$.

AC ELECTRICAL CHARACTERISTICS (continued)

over recommended operating conditions with 50- Ω output load, open loop operation, $I_{MOD} = 6$ mA, $I_{BIAS} = 5$ mA, and $R_{RZTC} = 30$ k Ω (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
τ_{APC}	$C_{APC} = 0.01$ μ F, $I_{PD} = 100$ μ A, PD coupling ratio CR = 1/40 ⁽²⁾		200		μ s
T_{OFF}	Rising edge of DIS to $I_{BIAS} \leq 0.1 \times I_{BIAS-NOMINAL}$ ⁽²⁾		2.4	5	μ s
T_{ON}	Falling edge of DIS to $I_{BIAS} \geq 0.9 \times I_{BIAS-NOMINAL}$ ⁽²⁾		1		ms
T_{INIT1}	Power-on to initialize	Power-on to registers ready to be loaded	20	250	ms
T_{INIT2}	Initialize to transmit	Register load STOP command to part ready to transmit valid data ⁽²⁾		2	ms
T_{RESET}	DIS pulse width	Time DIS must held high to reset part ⁽²⁾	100		ns
T_{FAULT}	Fault assert time	Time from fault condition to FLT high ⁽²⁾		50	μ s

(2) Assured by simulation over process, supply, and temperature variation.

TYPICAL CHARACTERISTICS

Typical operating condition is at $V_{CC} = 3.3$ V and $T_A = 25^\circ\text{C}$ (unless otherwise noted)

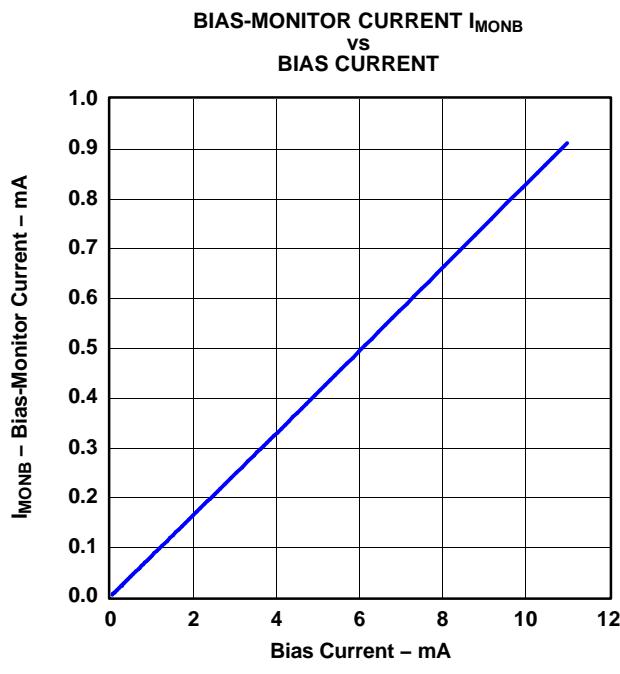


Figure 5.

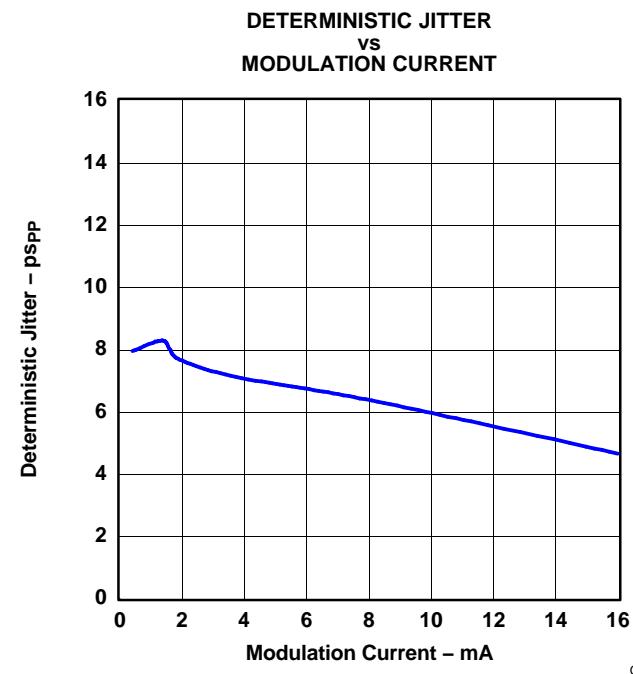


Figure 6.

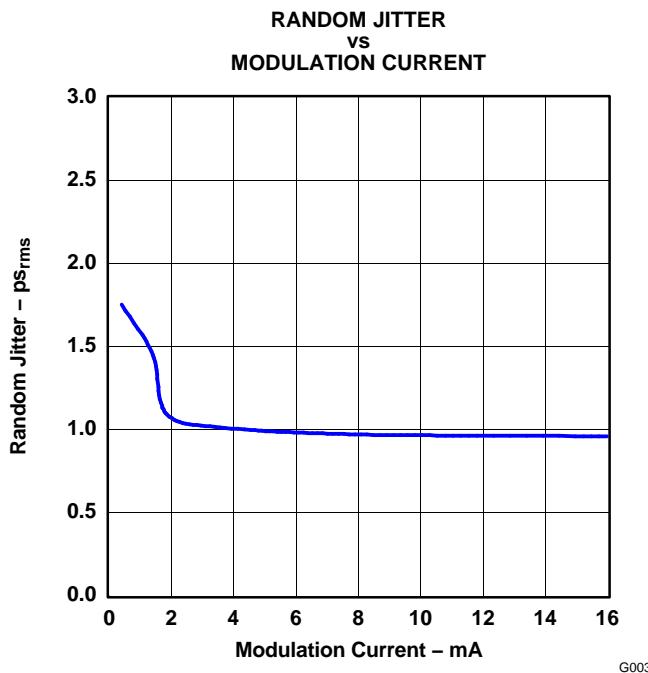


Figure 7.

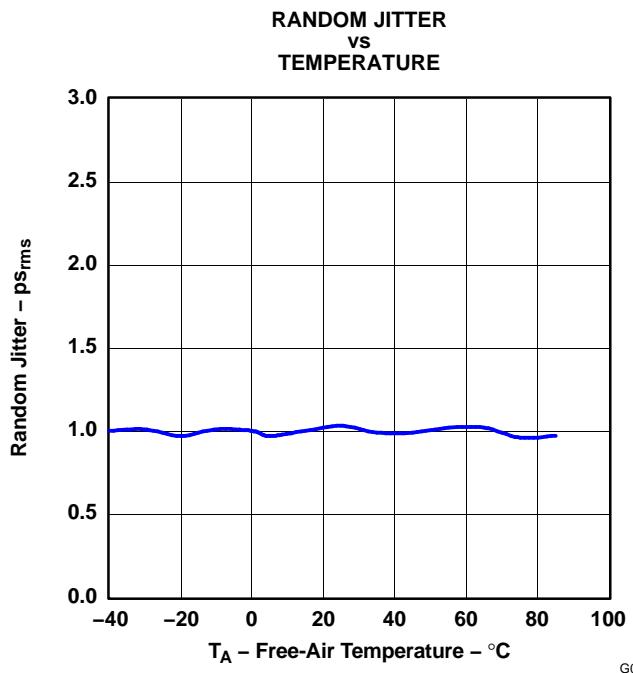


Figure 8.

TYPICAL CHARACTERISTICS (continued)

Typical operating condition is at $V_{CC} = 3.3$ V and $T_A = 25^\circ\text{C}$ (unless otherwise noted)

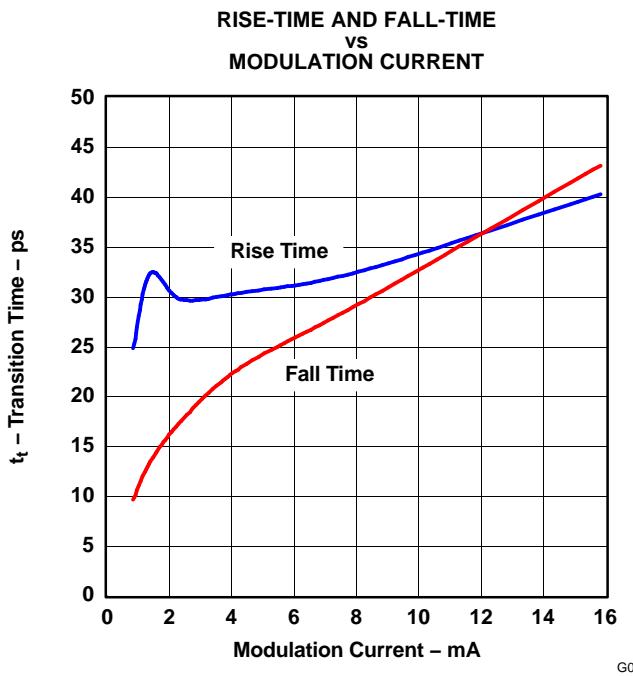


Figure 9.

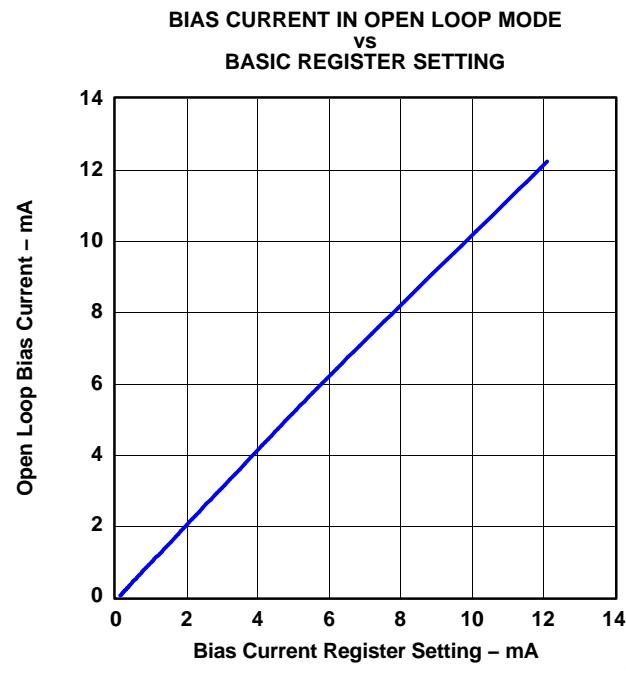


Figure 10.

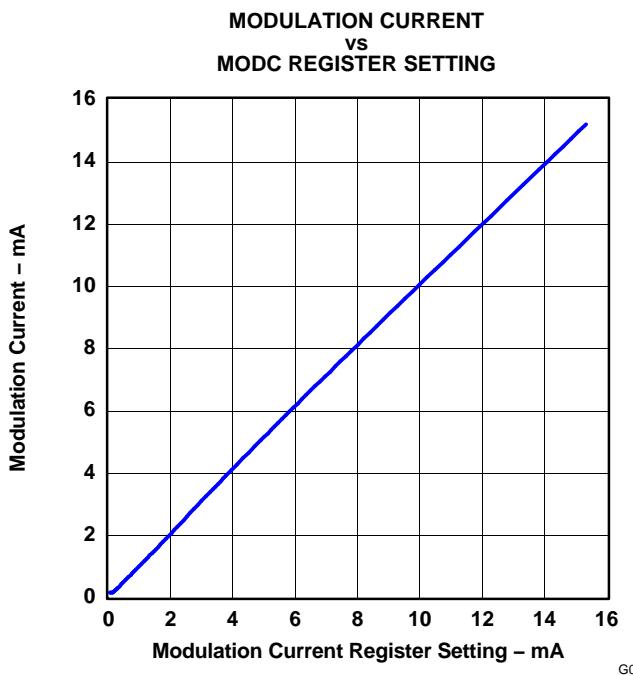


Figure 11.

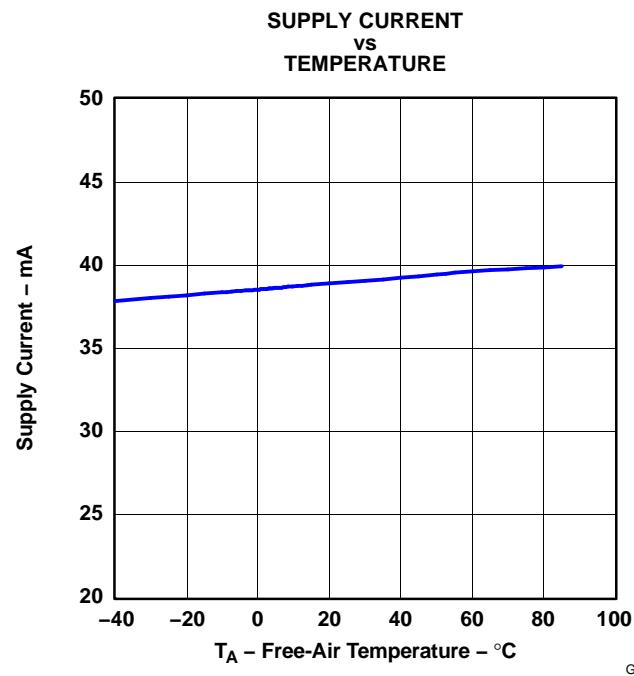


Figure 12.

TYPICAL CHARACTERISTICS (continued)

Typical operating condition is at $V_{CC} = 3.3$ V and $T_A = 25^\circ\text{C}$ (unless otherwise noted)

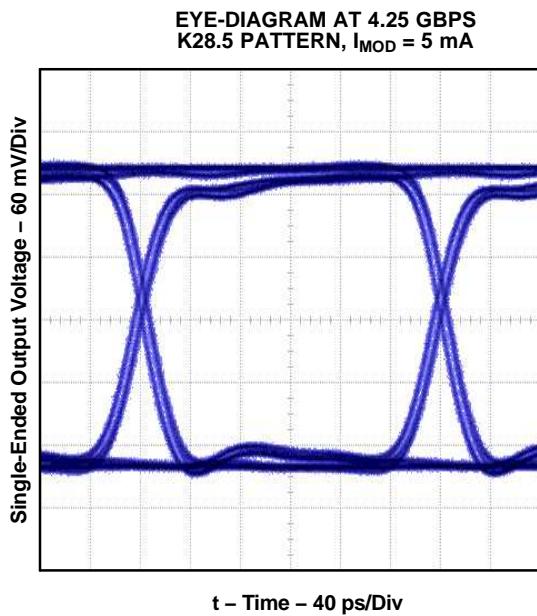


Figure 13.

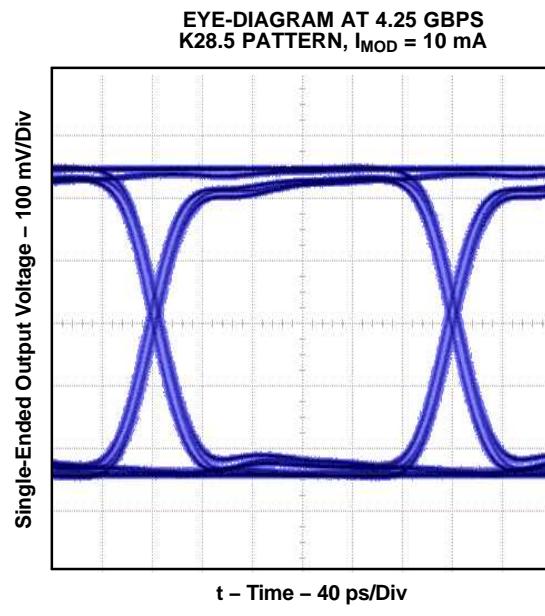


Figure 14.

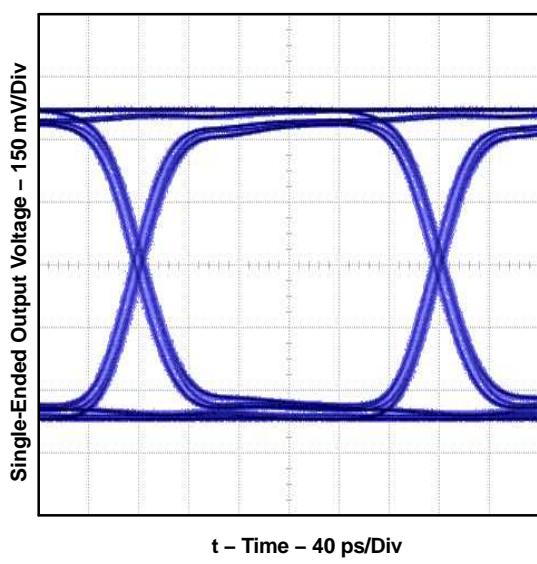


Figure 15.

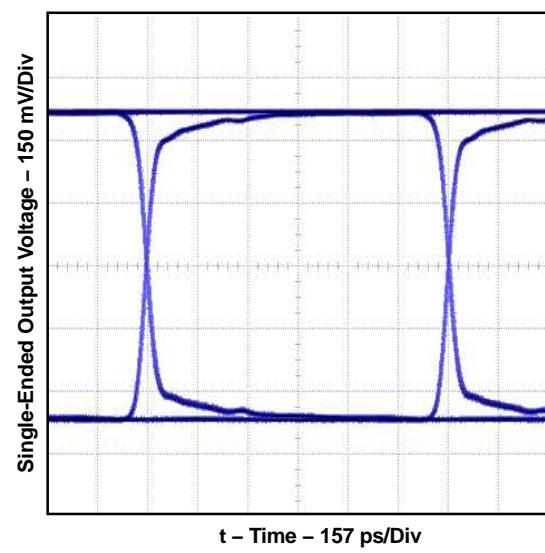


Figure 16.

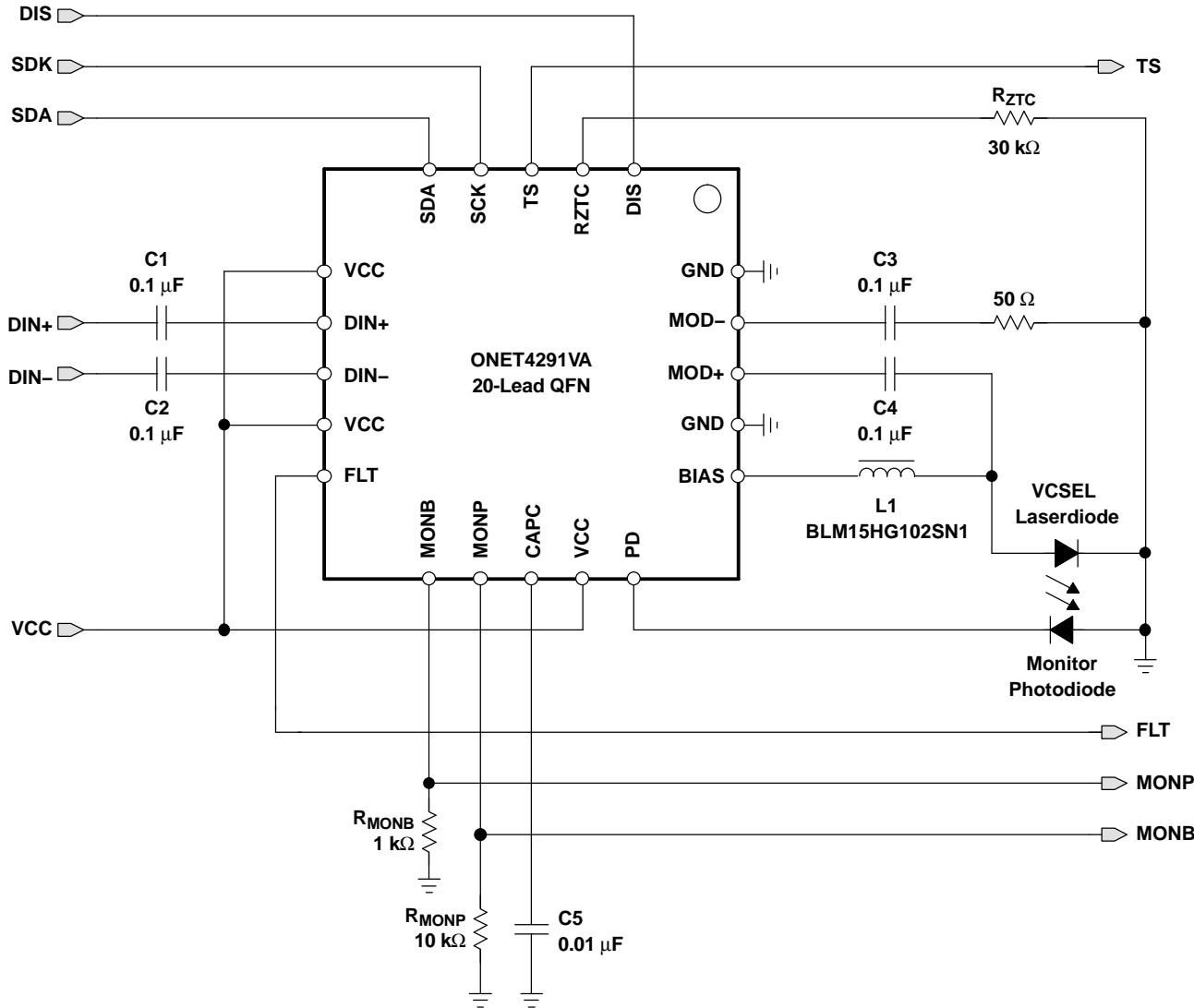
APPLICATION INFORMATION

Figure 17 shows a typical application circuit using the ONET4291VA with a common cathode VCSEL connected to ground.

The VCSEL driver is controlled via the 2-wire interface SDA/SCK by a microprocessor.

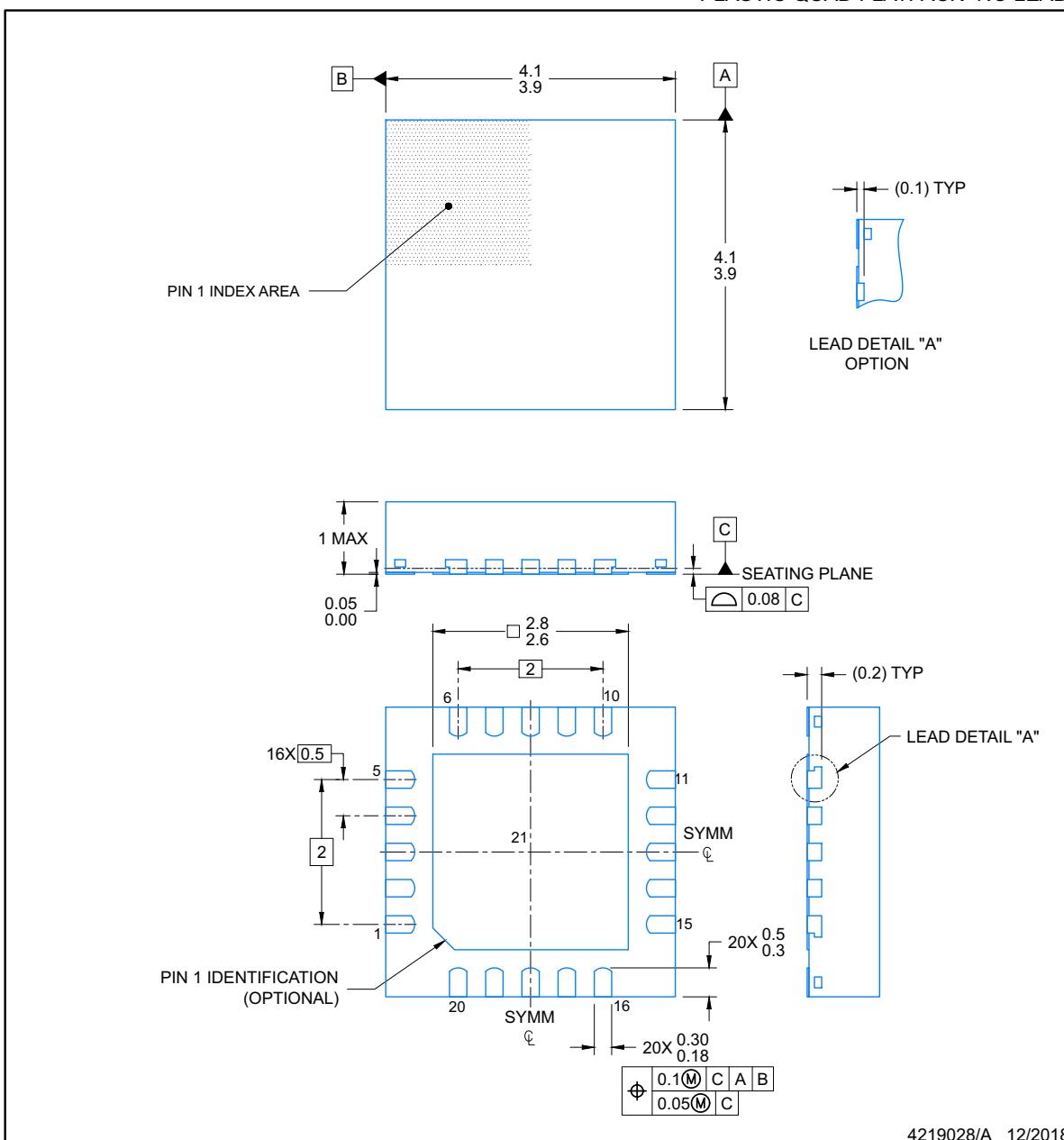
In a typical application, the FLT, MONB, MONP, and TS outputs are connected to the microcontroller for transceiver management purposes.

The component values in Figure 17 are typical examples and may be varied according to the intended application.

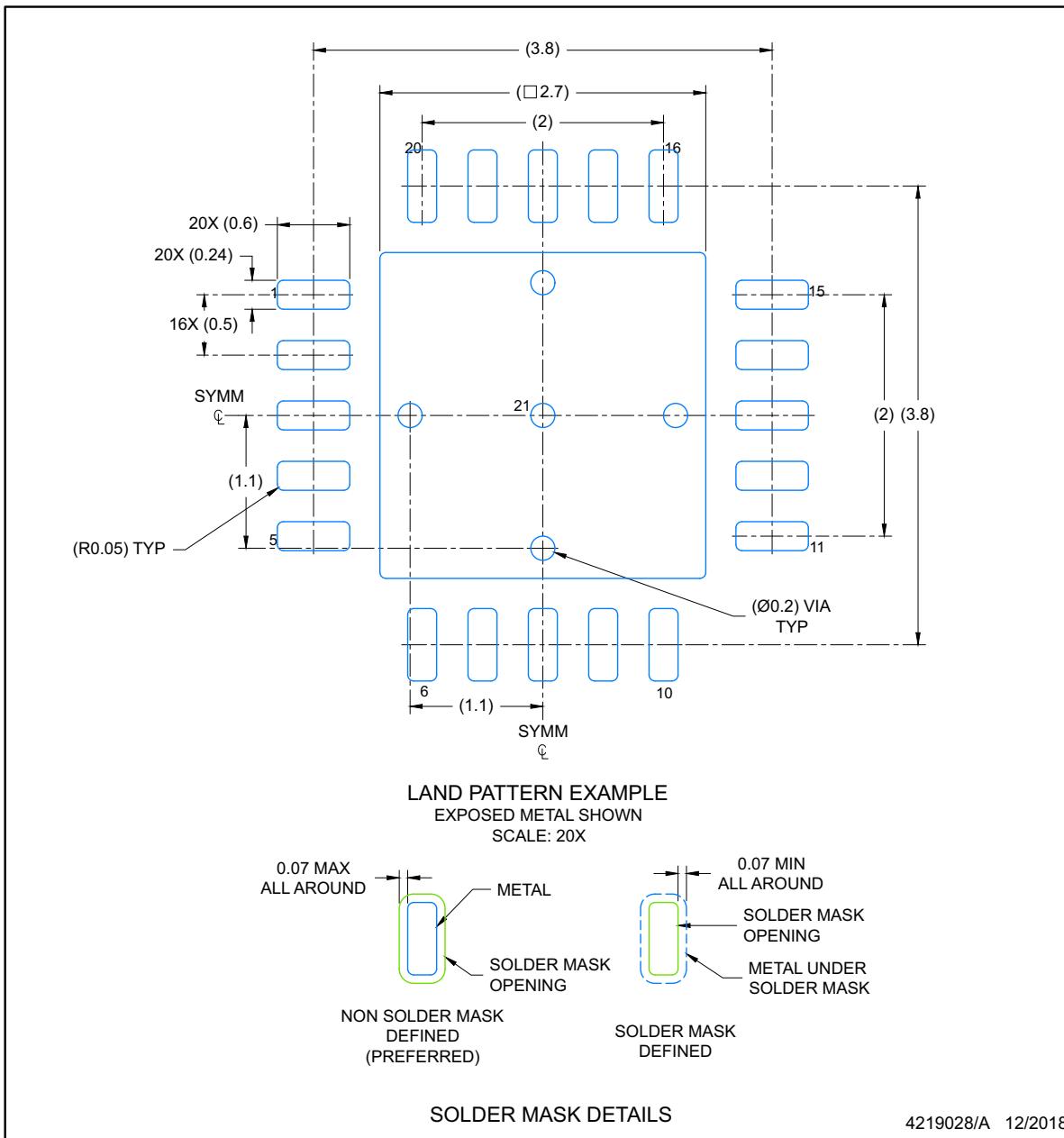


S0100-01

Figure 17. Basic Application Circuit With a Common Cathode VCSEL

RGP0020D
PACKAGE OUTLINE
VQFN - 1 mm max height
PLASTIC QUAD FLATPACK- NO LEAD

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

EXAMPLE BOARD LAYOUT
RGP0020D
VQFN - 1 mm max height
PLASTIC QUAD FLATPACK- NO LEAD


NOTES: (continued)

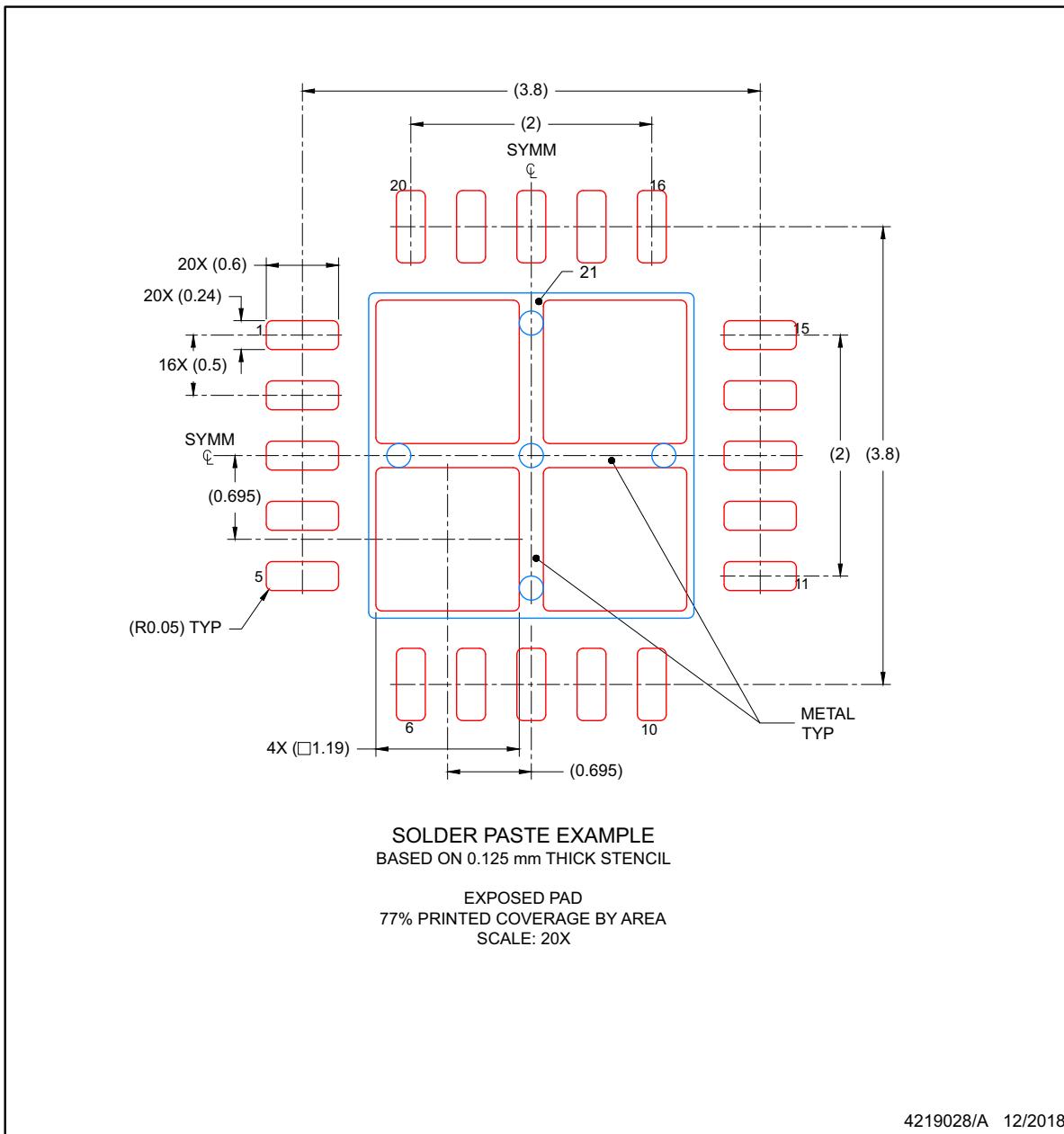
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RGP0020D

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK- NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
ONET4291VARGPR	ACTIVE	QFN	RGP	20	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ONET 4291V	Samples
ONET4291VARGPT	ACTIVE	QFN	RGP	20	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ONET 4291V	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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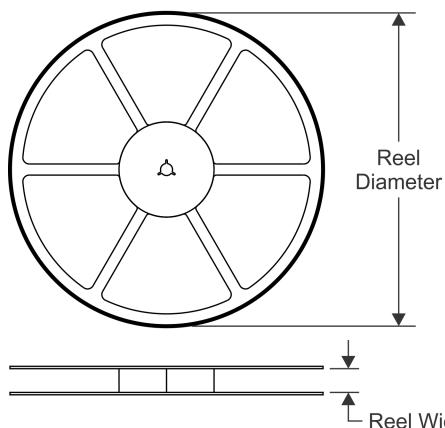
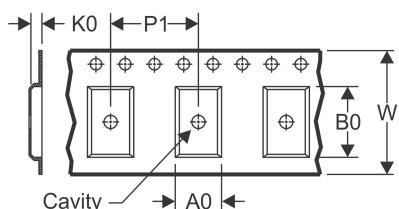
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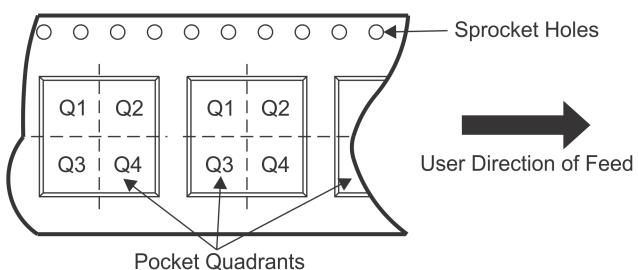
www.ti.com

PACKAGE OPTION ADDENDUM

10-Dec-2020

TAPE AND REEL INFORMATION
REEL DIMENSIONS

TAPE DIMENSIONS


A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ONET4291VARGPR	QFN	RGP	20	2500	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
ONET4291VARGPT	QFN	RGP	20	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ONET4291VARGPR	QFN	RGP	20	2500	853.0	449.0	35.0
ONET4291VARGPT	QFN	RGP	20	250	210.0	185.0	35.0

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